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(54) **REDUNDANT PIXEL ARCHITECTURE IN ILED DISPLAYS**

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**H01L 25/075** (2006.01)

**H01L 33/00** (2010.01)

(52) **U.S. Cl.**

CPC ..... **H01L 22/22** (2013.01); **H01L 25/0753** (2013.01); **H01L 33/0095** (2013.01)

(58) **Field of Classification Search**

CPC ..... H01L 22/22; H01L 25/0753; G09G 3/32; G09G 3/2003; G09G 2330/08; G09G 2300/0426; G09G 2300/0452  
See application file for complete search history.

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*Primary Examiner* — Jay C Chang

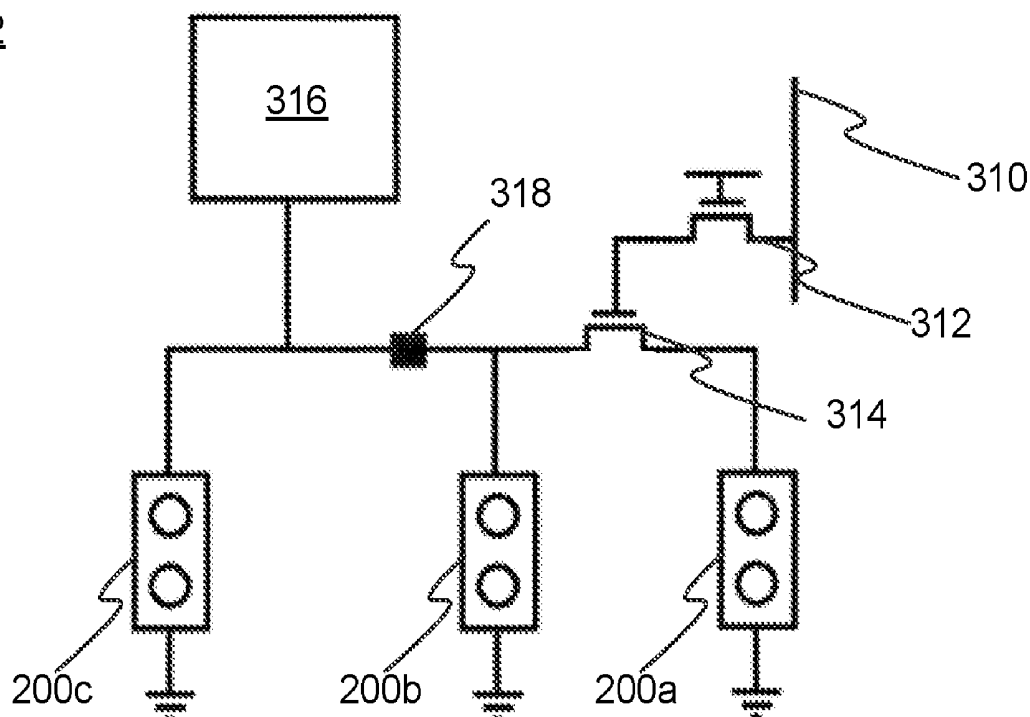
(74) *Attorney, Agent, or Firm* — Fenwick & West LLP

(57) **ABSTRACT**

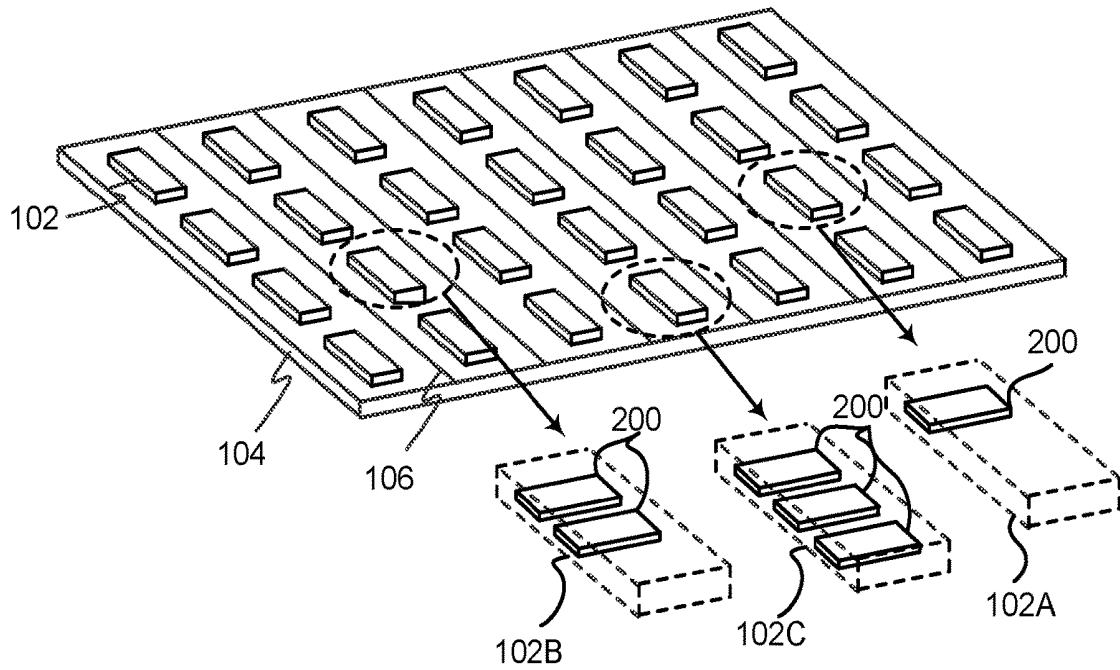
Described herein are ILED displays including redundancy in micro-light emitting diode (micro-LED) dies and methods of manufacturing the ILED displays. A micro-LED die emits light of a particular wavelength. The redundancy is added during manufacturing if defective micro-LED dies are identified. Additional micro-LED dies are included in inoperable sub-pixel assemblies to repair the inoperable sub-pixel assemblies that are identified to include defective micro-LED dies. An ILED display therefore includes at least one repaired sub-pixel assembly that includes two defective micro-LED dies and an operable micro-LED die that are coupled to separate branches of a current path from a current source.

**20 Claims, 5 Drawing Sheets**

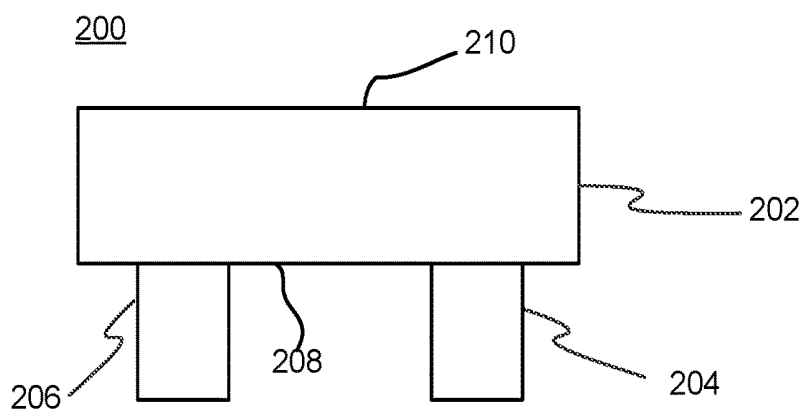
302



100



**Fig. 1**



**Fig. 2**

300

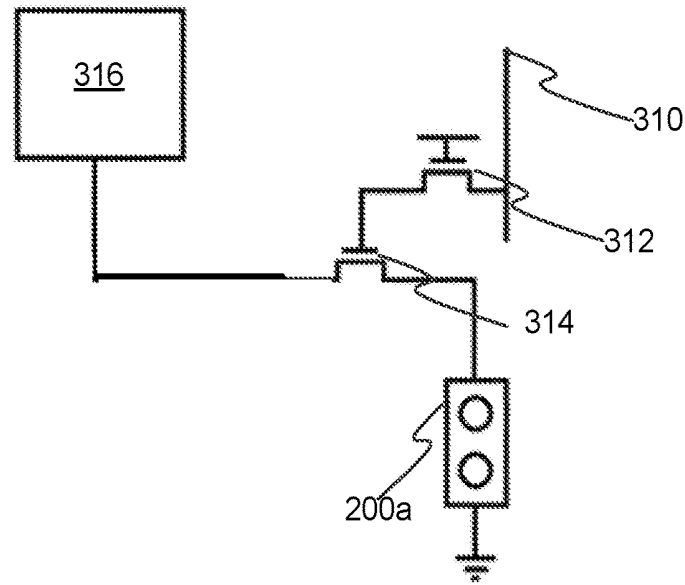


FIG. 3A

301

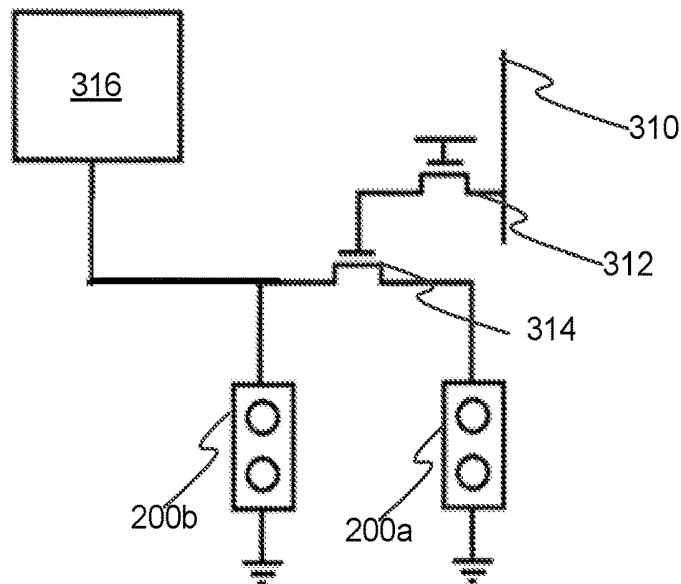


FIG. 3B

302

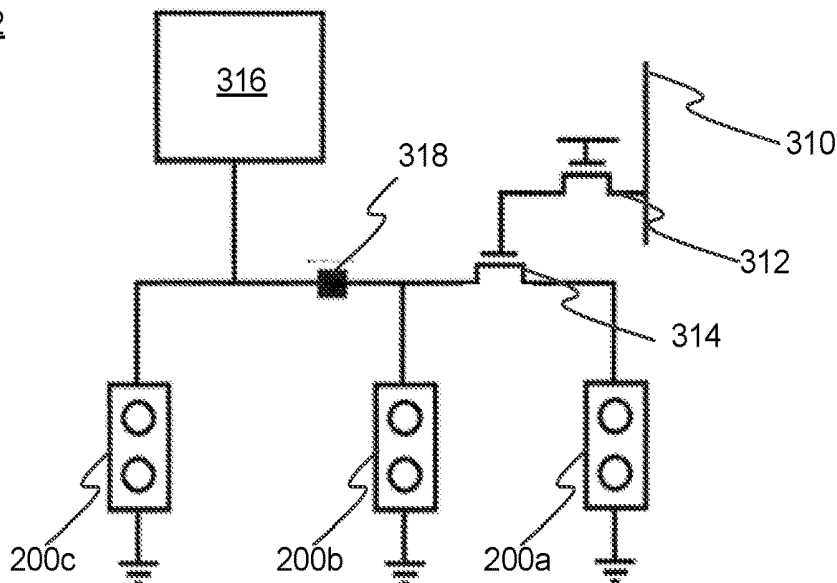


FIG. 3C

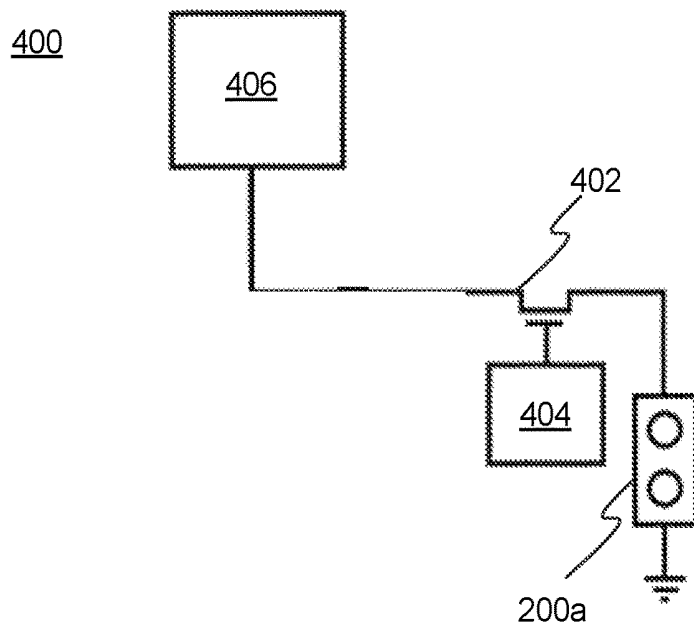


FIG. 4A

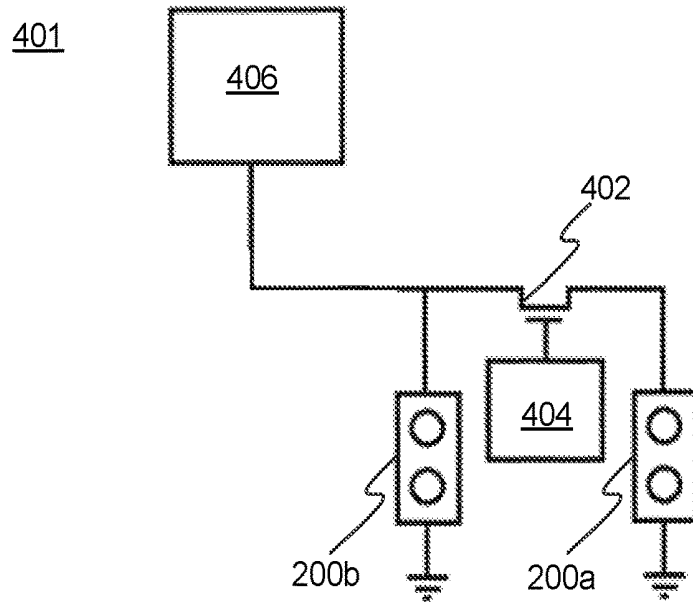


FIG. 4B

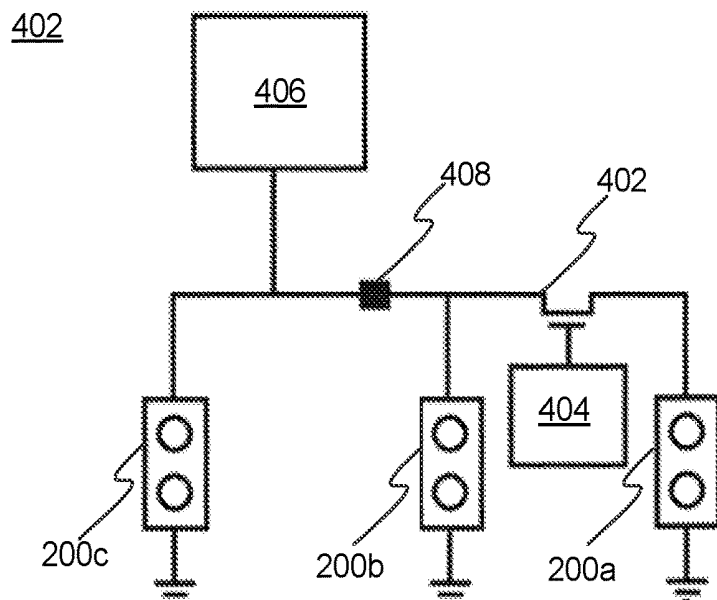


FIG. 4C

404

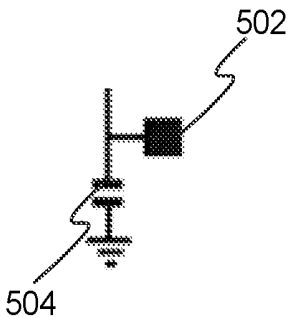


FIG. 5

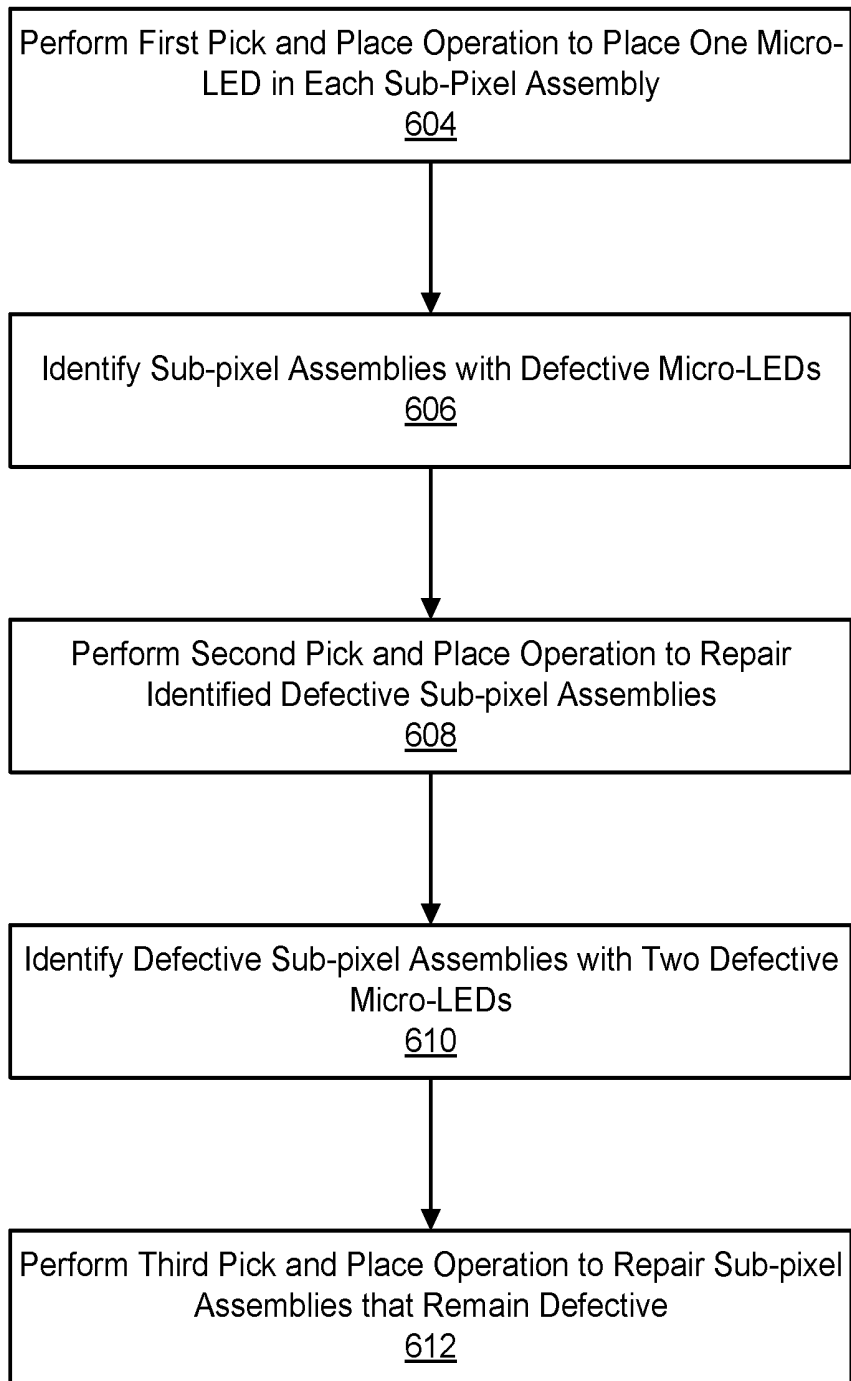


FIG. 6

## REDUNDANT PIXEL ARCHITECTURE IN ILED DISPLAYS

### CROSS REFERENCE TO RELATED APPLICATIONS

This application claims the benefit of Greek Application No. 20170100563, filed Dec. 12, 2017, which is incorporated by reference in its entirety.

### BACKGROUND

The disclosure relates to inorganic light emitting diode (ILED) displays, and more specifically, to pixel architectures in ILED displays.

Displays are ubiquitous and are a core component of wearable devices, smart phones, tablets, laptops, desktops, TVs and display systems. Common display technologies today range from Liquid Crystal Displays (LCDs) to more recent Organic Light Emitting Diode (OLED) Displays. OLED displays use organic or polymer materials that are sandwiched between two glass planes to produce light. In most portable devices (i.e. battery powered devices) the display uses a majority of the available battery power. Additionally, the most common user complaint for portable devices is insufficient display brightness. To extend battery life and improve brightness levels it is desirable to reduce power consumption and produce higher luminance emission from the light source.

Inorganic light emitting diode (ILED) displays can provide superior battery performance and enhanced brightness compared to OLED (organic light emitting diode) displays. In ILED displays, discrete standard LED dies that are made of inorganic materials are used to produce light. Each pixel of an ILED display includes three individual LED dies, namely, red, green and blue LED dies. However, it is challenging to manufacture smaller displays using this configuration because of smaller areas allocated to individual pixels. Additionally, it is not feasible to assemble many millions of pixels needed for smaller displays using standard assembly and manufacturing techniques. Furthermore, it is difficult and possibly not viable to test individually dies on an ILED wafer. The inevitability of defective LED dies significantly affects the manufacturing yield.

### SUMMARY

In one embodiment, a method for manufacturing a display device including sub-pixel assemblies. The method places a primary micro-light emitting diode (micro-LED) in each of the sub-pixel assemblies to create first sub-pixel assemblies. The method identifies second sub-pixel assemblies among the first sub-pixel assemblies, each second sub-pixel assembly with the primary micro-LED that is defective. The method places a first micro-LED in each of the second sub-pixel assemblies responsive to identifying the second sub-pixel assemblies. The method further identifies third sub-pixel assemblies among the second sub-pixel assemblies. Each third sub-pixel assembly is with the primary micro-LED and the first replacement micro-LED that are defective. Responsive to identifying the third sub-pixel assemblies, the method physically severs a current path to the primary micro-LED and the first replacement micro-LED in each of the third sub-pixel assemblies, and places a second replacement micro-LED in each of the third sub-pixel assemblies.

In one embodiment, a display device includes a first sub-pixel assembly and a second repaired sub-pixel assembly. The first sub-pixel assembly includes a defective micro-light emitting diode (micro-LED), a first operable micro-LED connected to a first current source, and a first switch coupled between the first operable micro-LED and the defective LED. The first switch is configured to disconnect the defective micro-LED from the first current source. The second repaired sub-pixel assembly comprises two defective micro-LEDs connected to a branch of a current path physically severed from a second current source, and a second operable micro-LED connected to another branch of the current path connected to the second current source.

In one embodiment, a display device is made by a method that places a primary micro-light emitting diode (micro-LED) in each of the sub-pixel assemblies to create first sub-pixel assemblies. The method identifies second sub-pixel assemblies among the first sub-pixel assemblies, each second sub-pixel assembly with the primary micro-LED that is defective. The method places a first micro-LED in each of the second sub-pixel assemblies responsive to identifying the second sub-pixel assemblies. The method further identifies third sub-pixel assemblies among the second sub-pixel assemblies. Each third sub-pixel assembly is with the primary micro-LED and the first replacement micro-LED that are defective. Responsive to identifying the third sub-pixel assemblies, the method physically severs a current path to the primary micro-LED and the first replacement micro-LED in each of the third sub-pixel assemblies, and places a second replacement micro-LED in each of the third sub-pixel assemblies.

### BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a schematic perspective view of a portion of an ILED display, according to one embodiment.

FIG. 2 illustrates a micro-LED die, according to one embodiment.

FIGS. 3A through 3C illustrate example sub-pixel assemblies, according to one embodiment.

FIGS. 4A through 4C illustrate example sub-pixel assemblies, according to one embodiment.

FIG. 5 illustrate an example memory element, according to one embodiment.

FIG. 6 illustrates an example process of manufacturing an ILED display, according to one embodiment.

The figures depict embodiments of the present disclosure for purposes of illustration only.

### DETAILED DESCRIPTION

Described herein are ILED display architecture that enables repairing of inoperable sub-pixel assemblies and ILED displays that include repaired sub-pixel assemblies using such architecture. At least one repaired sub-pixel assembly includes two defective micro-LED dies and an operable micro-LED die that are coupled to separate branches of a current path from a current source. Additional micro-LED dies are included in sub-pixel assemblies that are identified as defective during manufacturing to repair those sub-pixel assemblies.

FIG. 1 is a schematic perspective view of a portion of an ILED display 100, according to one embodiment. The ILED display 100 comprises a matrix of sub-pixel assemblies 102. A sub-pixel assembly 102 produces light for a pixel on an image displayed by the display 100. The sub-pixel assembly 102 may be a part of a pixel assembly and emits red light,

green light, or blue light. A sub-pixel assembly **102** includes at least one micro-LED die **200**. A sub-pixel assembly is coupled to a driving circuitry for driving the sub-pixel assembly to emit light. A micro-LED die may be an inorganic LED (ILED) die. More examples of sub-pixel assemblies are further described with respect to FIGS. **3A** through **5C**.

A micro-LED die is a light emitting element that produces light of a particular wavelength. As illustrated in FIG. **2**, a micro-LED die **200** includes a light emitter **202** that produces and emits light. The light emitter **202** includes a p-electrode **204** and an n-electrode **206**. In the illustrated example, the p- and n-electrodes **204**, **206** are formed on a same surface (e.g., a bottom surface **208**) of the micro-LED die **200**. Light is output from the opposite surface (e.g., a top surface **210**) of the micro-LED die **200**.

Referring back to FIG. **1**, to provide redundancy, a sub-pixel assembly **102** can include multiple micro-LED dies that emit the same colored light. For example, a sub-pixel assembly **102B** corresponding to a red sub-pixel can include two micro-LED dies that are configured to emit red light, one of which is defective. For an ILED display **100**, some sub-pixel assemblies (e.g., sub-pixel assembly **102A**) include one micro-LED die **200** whereas some sub-pixel assemblies (e.g., sub-pixel assemblies **102B**, **102C**) include multiple micro-LED dies **200**. Accordingly, different sub-pixel assemblies may include different numbers of micro-LED dies depending on whether one or more micro-LED dies in the sub-pixel assemblies are defective. In some embodiments, for a particular colored light, the number of micro-LED dies included in one sub-pixel assembly is limited to three. As further described below with reference to FIGS. **3A** through **4C**, the number of micro-LED dies included in one sub-pixel assembly is determined based on whether one or more micro-LEDs previously placed in the sub-pixel assembly are defective.

Accordingly, on the same ILED display **100**, different pixel assemblies **102** may include different numbers of micro-LED dies. In embodiments where the number of micro-LED dies included in one sub-pixel assembly is limited to three, a pixel assembly consisting of three sub-pixel assemblies can include micro-LED dies that are in the range of three to nine because each sub-pixel can include one to three micro-LED dies.

As illustrated in FIG. **1**, the pixel assemblies **102** are assembled onto a display substrate **104**. The display substrate **104** can be a silicon or glass panel including a layer of switches such as n-type or p-type TFTs (thin-film transistors) or MOSFETs (metal-oxide-semiconductor field-effect transistors). Electrical circuitries **106** and electrodes (not shown) of the display substrate **104** are formed on the substrate **104**. The electrodes of the display substrate **104** are connected to the electrical circuitries **106** which are connected to electrodes of the micro-LED dies in the pixel assemblies. In order to prevent obfuscation, other components of the ILED display **100** such as a driving IC block, a power module, and the like are not shown.

FIGS. **3A** through **3C** illustrate example sub-pixel assemblies **300** through **302**, according to one embodiment. The sub-pixel assembly **300** includes one operative micro-LED die **200a** placed during a first pick and place operation of micro-LED dies. A pick and place operation described herein refers to an operation of picking up one or more micro-LED dies from a substrate and placing these micro-LED dies onto a display substrate. Micro-LEDs for producing the same color is generally fabricated on a fabrication substrate. Hence, in order to form a pixel assembly including

micro-LED dies producing different colors, these micro-LEDs are picked up from the fabrication substrate or a temporary carrier substrate and then placed onto desired locations on the display substrate. If the micro-LED die **200a** is operational, no additional micro-LED dies need to be picked and placed in the circuit of FIG. **3A**, and hence, the configuration of FIG. **3A** becomes the final configuration of the sub-pixel assembly.

In the example of FIG. **3A**, the sub-pixel assembly **300** includes a micro-LED die **200a**, a control line **310**, a first TFT (thin-film transistor) **312**, a second TFT **314**, and a driving circuitry **316**. The TFTs **312**, **314** are switches that can be turned on or off using a bias gate-to-source voltage applied between their respective gate and source.

The TFT **312** is used to control switching on and off of the TFT **314**. The TFT **314** is used to control connecting or disconnecting the micro-LED die **200a** to the driving circuitry **316**. The TFT **312** is controlled by a control signal applied to the gate of the TFT **312**. This control signal may be a scan signal used to turn on or off a row of sub-pixel assemblies in a matrix of sub-pixel assemblies. If the TFT **312** is switched off, the TFT **314** is disconnected from the control line **310**. If the TFT **312** is switched on, the TFT **314** is connected to the control line **310**. A control voltage applied to the control line **310** is applied to the gate of the TFT **314** and this control voltage is programmed to switch on or off the TFT **314**. The control voltage applied to the control line **310** is configured to have a value that is determined according to the topology of the sub-pixel assembly. For example, if the micro-LED die **200a** is operative such that the sub-pixel assembly is of the topology illustrated in FIG. **3A**, the control voltage applied to the control line **310** is configured to have a value to turn on the TFT **314**. As another example, if the micro-LED die **200a** is detected to be defective during manufacture such that the sub-pixel assembly is of the topology illustrated in FIG. **3B**, the control voltage applied to the control line **310** is configured to have a value to turn off the TFT **314**. If the TFT **314** is switched on, the micro-LED **200a** is connected to the driving circuitry **316**. The driving circuitry **316** is controlled by a control logic (not shown) to supply a driving current to drive the micro-LED die **200a** to emit light. If the TFT **314** is switched off, the micro-LED **200a** is disconnected from the driving circuitry **316**.

However, if the micro-LED die **200a** turns out to be defective (e.g., not emitting light when turned on, or emitting light when turned off), a repair operation is performed. The repair operations may be performed in multiple levels or sequences, as required. If the micro-LED die **200a** of FIG. **3A** is identified as being defective, a second pick and place operation is performed to place another micro-LED die **200b** as illustrated in FIG. **3B** to form sub-pixel assembly **301**. The sub-pixel assembly **301** includes the defective micro-LED die **200a**, the micro-LED die **200b**, the control line **310**, the first TFT **312**, the second TFT **314**, and the driving circuitry **316**. The micro-LED die **200b** and the micro-LED die **200a** are coupled to the opposite terminals of the second TFT **314**. That is, one of the drain and source of the TFT **314** is coupled to the micro-LED die **200a** and the other is coupled to the micro-LED die **200b**.

Compared to the sub-pixel assembly **300** illustrated in FIG. **3A**, the sub-pixel assembly **301** illustrated in FIG. **3B** includes the micro-LED die **200b** added by the second pick and place operation to repair the subpixel assembly **301**. The TFT **314** is controlled to prevent the micro-LED die **200a** from being connected to the driving circuit **316**. For example, an external circuit coupled to the control line **310**



is set to send a low voltage (e.g., 0) over the control line **310** so that the TFT **314** is turned off when the TFT **312** is turned on. By turning off the TFT **314**, no driving current is provided from the driving circuitry **316** to the defective micro-LED die **200a**.

If the added micro-LED die **200b** is also defective, a second repair operation involving third pick and place operation may be performed on the sub-pixel assembly **301** to form a sub-pixel assembly **302**, as illustrated in FIG. 3C. In addition to adding the micro-LED die **200c**, a laser cutting operation is performed at laser cut point **318** to cut off the output line from the driving circuit **316** to the micro-LED **200b**. Compared to the sub-pixel assembly **301** illustrated in FIG. 3B, the sub-pixel assembly **302** illustrated in FIG. 3C includes the micro-LED die **200c** for replacing the micro-LED die **200a** and the micro-LED die **200b**.

The TFTs **312** and **314** may be of the same type (e.g., amorphous silicon, IGZO, or low temperature polycrystalline silicon TFTs).

FIGS. 4A through 4C illustrate example sub-pixel assemblies **400** through **402**, according to one embodiment. The repairing operations associated with the sub-pixel assemblies **400** through **402** and the circuit structure of FIGS. 4A through 4C are substantially the same as those of FIGS. 3A through 3C except that a single TFT **402** having its gate connected to a memory element **404**. The memory element **404** is programmed to store a value (e.g., a bias charge) that either switches on or off the TFT **402**. The TFT **402** is used to connect or disconnect the micro-LED die **200a** to the driving circuitry **406**. The memory element can be programmed during display fabrication or be refreshed periodically during the normal operation of the ILED display device **100**.

Compared to the embodiments illustrated in FIGS. 3A through 3C, the embodiments illustrated in FIGS. 4A through 4C include fewer components. By including memory elements in individual sub-pixel assemblies, the embodiments illustrated in FIGS. 4A through 4C do not need additional memory elements in driving integrated circuit (IC) blocks. When the memory element is programmed only once, there is no increase in power consumption due to the repair operation.

FIG. 5 illustrates an example memory element, according to one embodiment. The memory element **404** includes a capacitor **504** and a bias pad **502**. The capacitor **504** is coupled between the gate of the TFT **402** and the ground. In addition, the bias pad **502** is coupled to the gate of the TFT **402**. The capacitor **504** can be charged via the bias pad **502**. The capacitance of the capacitor **504** and the TFT **402** are selected such that the charge stored in the capacitor **504** can be maintained to a threshold level to turn on the switch **402** over a time interval. For example, the charge stored in the capacitor **504** is preferably greater than a threshold to turn on the TFT **402** over the life time of the ILED display.

FIG. 6 illustrates an example process of manufacturing an ILED display, according to one embodiment. The process can involve a single assembly station that performs a plurality of placement cycles (e.g. pick, place, test). The ILED display manufactured according to the illustrated process includes sub-pixel assemblies, some of which may undergo repairing operation.

After micro-LED dies are fabricated on a fabrication substrate, the process performs a first pick and place operation **604** to place a single micro-LED die in each sub-pixel assembly on a display substrate. A sub-pixel assembly includes one micro-LED die. The sub-pixel assemblies **300**

and **400** illustrated in FIGS. 3A and 4A, respectively, are example sub-pixel assembly configurations created.

The display substrate includes a semiconductor layer that includes a plurality of switches (e.g., TFTs, MOSFETs) for controlling whether to connect a particular micro-LED die to a driving circuit. The micro-LED dies may be placed on the display substrate such that they form a matrix (e.g., square matrix) of micro-LED dies corresponding to sub-pixel locations on the display. The placement may start from a corner of the ILED display.

The picking and placing may be performed in iterations until all sub-pixel assemblies corresponding to one colored light are formed on the display substrate. The PUT moves sequentially when performing the picking as well as when performing the placing of micro-LED dies. That is, the PUT moves to pick a micro-LED die from the wafer (1) that is adjacent to the micro-LED die that was picked in the previous iteration. The PUT moves to place the micro-LED to a location on the display substrate that is next to the micro-LED die that was placed in the previous iteration.

Then sub-pixel assemblies with defective micro-LEDs are identified **606**.

The defective sub-pixel assemblies include defective, missing, or contaminated micro-LED dies. Such defects may be termed "killer defects." For example, the entire display is driven such that all sub-pixel assemblies are turned on to emit light or turned off to emit no light. If a sub-pixel assembly does not emit light when turned on or emits light when turned off, it is identified as a defective sub-pixel assembly. The process may use a camera to identify the defective sub-pixel assemblies. The camera can measure a light profile. If a sub-pixel assembly emits light having an intensity that is less than a threshold intensity corresponding to a driving current, the sub-pixel is determined as defective.

A second pick and place operation may then be performed **608** to place a replacement micro-LED die into each identified defective sub-pixel assembly to repair the identified sub-pixel assemblies. The sub-pixel assemblies **301** and **401** illustrated in FIGS. 3B and 4B, respectively, are example sub-pixel assembly configurations created. Similar to the picking and placing of micro-LEDs to create **604** sub-pixel assemblies, the picking and placing of micro-LEDs to repair **608** defective sub-pixel assemblies may be performed in iterations until all sub-pixel assemblies corresponding to one colored light are formed on the display substrate.

The locations of the replacement micro-LED dies are recorded because the corresponding sub-pixel assemblies are driven in a manner different from the other sub-pixel assemblies that do not include the replacement micro-LED dies. For example, a map of the locations of the micro-LED dies is generated and stored. The map includes information that provides a basis for controlling the sub-pixel assemblies. For example, sub-pixel assemblies that include the replacement micro-LED dies can be identified from the map during a frame programming phase. The sub-pixel assemblies that include the replacement micro-LED dies are controlled such that the replacement micro-LED dies rather than the primary micro-LED dies are turned on in order to enable the sub-pixel assemblies to emit light. For ILED displays that use control signals to turn on or off the sub-pixel assemblies, a control module (e.g., a driving IC block) generates different control signals to control sub-pixel assemblies that include the replacement micro-LED dies and sub-pixel assemblies that include only the primary micro-LED dies. For ILED displays that use memory elements to turn on or off the sub-pixel assemblies, the bias charge stored in the memory elements of the identified

sub-pixel assemblies are reversed so that the replacement micro-LED dies rather than the primary micro-LED dies are driven by the driving current.

Then defective sub-pixel assemblies with two defective micro-LED dies are identified **610**. That is, an identified sub-pixel assembly includes the primary micro-LED die and the replacement micro-LED die that are both defective. The identification **610** is similar to the identification **606** described above. Details are omitted for brevity.

The process performs a third pick and place operation **612** to place a second replacement micro-LED die into each identified defective sub-pixel assembly to repair the identified sub-pixel assemblies. The second replacement micro-LED dies provide further redundancy. In addition, the process creates laser cut points to provide electrical isolation. The sub-pixel assemblies **302** and **402** illustrated in FIGS. **3C** and **4C**, respectively, are example sub-pixel assembly configurations created. Similar to the picking and placing performed to create sub-pixel assemblies and to repair defective sub-pixel assemblies, the picking and placing may be performed in iterations until all sub-pixel assemblies corresponding to one colored light are formed on the display substrate.

In addition, the process creates laser cut points at predetermined locations within sub-pixel assemblies identified to include two defective micro-LED dies to provide electrical isolation. In particular, in a sub-pixel assembly, the laser cut point electrically isolates the first replacement micro-LED die and the primary micro-LED die from the driving circuitry. Only the second replacement micro-LED die is connected to the driving circuitry. As such, the second replacement micro-LED dies rather than the primary micro-LED dies or the first replacement micro-LED dies are driven by a driving current in order to turn on the sub-pixel assemblies to emit light.

In some embodiments, the above-described process creates, tests, and repairs sub-pixel assemblies for one colored light. The same process is repeated to create, test, and repair sub-pixel assemblies for the other two colored light. In some embodiments, the above-described process creates sub-pixel assemblies for all three colored light concurrently. Subsequently, the process tests the created sub-pixel assemblies for all three colored light concurrently, and repairs sub-pixel assemblies for all three colored light concurrently.

The language used in the specification has been principally selected for readability and instructional purposes, and it may not have been selected to delineate or circumscribe the inventive subject matter. It is therefore intended that the scope of the patent rights be limited not by this detailed description, but rather by any claims that issue on an application based hereon. Accordingly, the disclosure of the embodiments is intended to be illustrative, but not limiting, of the scope of the patent rights, which is set forth in the following claims.

What is claimed is:

1. A method for manufacturing a display device comprising sub-pixel assemblies, the method comprising:
  - placing a primary micro-light emitting diode (micro-LED) in each of the sub-pixel assemblies to create first sub-pixel assemblies;
  - identifying second sub-pixel assemblies among the first sub-pixel assemblies, the primary micro-LED of each second sub-pixel assembly identified as being defective by at least supplying current via a switch;
  - responsive to identifying the second sub-pixel assemblies;

- turning off the switch to disconnect supply of the current to the primary micro-LED of each second sub-pixel assembly; and
  - placing a first replacement micro-LED in each of the second sub-pixel assemblies;
  - identifying third sub-pixel assemblies among the second sub-pixel assemblies, the primary micro-LED and the first replacement micro-LED of each third sub-pixel assembly being defective;
  - responsive to identifying the third sub-pixel assemblies:
    - physically severing a current path to the primary micro-LED and the first replacement micro-LED in each of the third sub-pixel assemblies, and
    - placing a second replacement micro-LED in each of the third sub-pixel assemblies.
2. The method of claim 1, wherein the current is supplied by a driving circuitry.
3. The method of claim 2, wherein placing the primary micro-LED comprises coupling the primary micro-LED to a first terminal of the switch.
4. The method of claim 3, wherein placing the first replacement micro-LED comprises coupling the first replacement micro-LED to a second terminal of the switch.
5. The method of claim 2, wherein physically severing a current path to the primary micro-LED and the first replacement micro-LED comprises creating a laser cut along the current path between the driving circuitry and the first replacement micro-LED.
6. The method of claim 2, wherein placing the second replacement micro-LED comprises coupling the second replacement micro-LED to the driving circuitry.
7. The method of claim 2, wherein identifying the second sub-pixel assemblies further comprises:
  - measuring an intensity of light emitted by each of the first sub-pixel assemblies, and
  - identifying one or more of the first sub-pixel assemblies emitting light having the intensity lower than a threshold intensity as the second sub-pixel assemblies.
8. The method of claim 2, further comprising:
  - programming a memory element coupled to the switch in each of the second sub-pixel to turn off the switch.
9. The method of claim 1, further comprising storing a location of each identified second sub-pixel assembly.
10. The method of claim 1, wherein identifying the third sub-pixel assemblies comprises regulating a driving circuitry to supply the current to the first replacement micro-LED in each of the second sub-pixel assemblies.
11. The method of claim 10, wherein identifying the third sub-pixel assemblies further comprises:
  - measuring an intensity of light emitted by each of the second sub-pixel assemblies, and
  - identifying one or more of the second sub-pixel assemblies emitting light having the intensity lower than a threshold intensity as the third sub-pixel assemblies.
12. A display device, comprising:
  - a first repaired sub-pixel assembly comprising:
    - a defective micro-light emitting diode (micro-LED) coupled to a first current source,
    - a first operable micro-LED connected to the first current source, and
    - a first switch coupled between the first operable micro-LED and the defective LED, the first switch configured to be turned off to disconnect the defective micro-LED from the first current source; and
  - a second repaired sub-pixel assembly comprising:
    - two defective micro-LEDs connected to a branch of a current path physically severed from a second cur-

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rent source, the branch of the current path connected to a third current source separate from the second current source, and

- a second operable micro-LED connected to another branch of the current path connected to the second current source.

13. The display device of claim 12, wherein the second repaired sub-pixel assembly comprises a laser cut point severing the second current source from the two defective micro-LEDs.

14. The display device of claim 12, wherein the first repaired sub-pixel assembly comprises a second switch controlled by a control signal to turn on or turn off the first switch.

15. The display device of claim 12, further comprising: an unrepaired sub-pixel assembly comprising:

- a third operable micro-LED, and  
a second switch coupled between the third operable micro-LED and the third current source, the second switch configured to connect the third operable micro-LED to the third current source.

16. The display device of claim 15, wherein a first control signal to control the first switch is reverse of a second control signal to control the second switch.

17. The display device of claim 15, wherein the first repaired sub-pixel assembly comprises a first memory element to control the first switch to turn on or off, and the unrepaired sub-pixel assembly comprises a second memory element to control the second switch to turn on or off.

18. The display device of claim 17, wherein the each of the first memory element and the second memory element comprises a capacitor and a bias pad coupled to the capacitor.

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19. The display device of claim 17, wherein the first memory element stores a first bias charge, and the second memory element stores a second bias charge that is reverse of the first bias charge.

20. A display device made by a method comprising:

placing a primary micro-light emitting diode (micro-LED) in each of a plurality of sub-pixel assemblies to create first sub-pixel assemblies;

identifying second sub-pixel assemblies among the first sub-pixel assemblies, the primary micro-LED of each second sub-pixel assembly identified as being defective by at least supplying current via a switch;

responsive to identifying the second sub-pixel assemblies:

turning off the switch to disconnect supply of the current to the primary micro-LED of each second sub-pixel assembly, and

placing a first replacement micro-LED in each of the second sub-pixel assemblies;

identifying third sub-pixel assemblies among the second sub-pixel assemblies, the primary micro-LED and the first replacement micro-LED of each third sub-pixel assembly being defective;

responsive to identifying the third sub-pixel assemblies:

physically severing a current path to the primary micro-LED and the first replacement micro-LED in each of the third sub-pixel assemblies, and

placing a second replacement micro-LED in each of the third sub-pixel assemblies.

\* \* \* \* \*

专利名称(译)	ILED显示器中的冗余像素架构		
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#### 摘要(译)

在此描述的是包括微发光二极管 ( micro-LED ) 管芯中的冗余的ILED显示器及其制造方法。微型LED芯片发射特定波长的光。如果发现有缺陷的微型LED管芯,则会在制造过程中添加冗余。在无法操作的子像素组件中包含其他微型LED芯片,以修复被识别为包括有缺陷的微型LED芯片的无法工作的子像素组件。因此,ILED显示器包括至少一个修复的子像素组件,该组件包括两个缺陷的微型LED管芯和可操作的微型LED管芯,它们耦合到来自电流源的电流路径的单独分支。

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